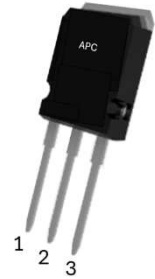
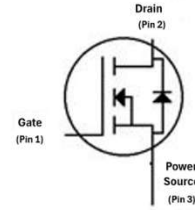




SiC Power MOSFET with Ceramic Isolated Baseplate Tab

AMR1k0V170E1i



Applications:

- Solar Inverters
- Uninterrupted power supplies
- Switch mode power supplies
- Motor drives

Features:

- High blocking voltage with low on-resistance
- High switching speed with low capacitance
- Very low switching losses
- Excellent avalanche ruggedness
- Very fast and robust intrinsic body diode with low reverse recovery
- 0V turn-off V_{GS} for gate driving ease
- RoHS compliant

Absolute Maximum Ratings ($T_{amb}=25^{\circ}C$, unless specified otherwise)

Symbol	Parameter	Value	Unit
V_{DSmax}	Drain-source voltage	1700	V
V_{GSmax}	Gate-source voltage, maximum transient voltage	-10/+27	
V_{GSmax}	Gate-source voltage, maximum static voltage	-8/+24	
V_{GSop}	Gate-source voltage	-5/+20	
I_D	Continuous drain current ($V_{GS} = 20V$)	5.7	A
	Continuous drain current ($V_{GS} = 20V$, $TC = 100^{\circ}C$)	4	
$I_{D(pulse)}$	Pulsed drain current (Pulse width limited by T_{jmax})	14	A
P_{tot}	Power dissipation	100	W
T_j	Operating junction temperature	-55 to 175	$^{\circ}C$
T_{stg}	Storage temperature	-55 to 175	$^{\circ}C$
T_L	Soldering temperature	260	$^{\circ}C$
M	Mounting torque	0.7	Nm

Thermal Resistances

Symbol	Parameter	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal Resistance	-	TBD	-	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-ambient thermal Resistance	-	-	TBD	$^{\circ}C/W$

Static Electrical Characteristics ($T_A = 25^\circ\text{C}$, unless specified otherwise)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 100\mu A$	1700	/	/	V
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 500\mu A^a$	2.0	2.6	4.0	
		$V_{DS} = V_{GS}, I_D = 500\mu A,$ $T_j = 175^\circ\text{C}^a$	-	1.8	-	
I_{DSS}	Drain-Source Leakage current	$V_{DS} = 1700V, V_{GS} = 0V$	-	1	100	μA
I_{GSS}	Gate-Source leakage current	$-10V < V_{GS} < 27V$	-	1	100	nA
$R_{DS(on)}$	Drain-Source ON Resistance	$V_{GS} = 20V, I_D = 2A$	-	1.0	1.2	Ω
		$V_{GS} = 20V, I_D = 2A,$ $T_j = 175^\circ\text{C}$	-	1.5	-	
g_{fs}	Transconductance	$V_{DS} = 20V, I_D = 2A$	-	1.0	-	S
		$V_{DS} = 20V, I_D = 2A,$ $T_j = 175^\circ\text{C}$	-	1.2	-	
$R_{g(int)}$	Internal Gate Resistance	$f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	10	-	Ω
EAS	Avalanche Energy	$L = 5\text{mH}, V_{DD} = 50V$	-	150	-	mJ

^a pre-condition V_{th} , as per JEDEC standard JEP183A, (Revision of JEP183 January 2021)

Dynamic Characteristics ($T_A = 25^\circ\text{C}$, unless specified otherwise)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0V, V_{DS} = 1000V,$ $f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	227	-	pF
C_{oss}	Output capacitance		-	12.5	-	
C_{rss}	Reverse transfer capacitance		-	2	-	
E_{oss}	C_{oss} stored energy		-	7.7	-	μJ
Q_{GS}	Gate to source charge	$V_{DD} = 1200V, I_D = 2A,$ $V_{GS} = -5/+20V,$ $I_{GS} = 1\text{mA}$	-	1.67	-	nC
Q_{GD}	Gate to drain charge		-	9.2	-	
Q_G	Total gate charge		-	16.7	-	

Switching Characteristics ($T_A = 25\text{ }^\circ\text{C}$, unless specified otherwise)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on delay time		-		-	ns
t_r	Rise time		-		-	
$t_{d(off)}$	Turn-off delay time		-		-	
t_f	Fall time		-		-	
E_{on}	Turn-on switching energy		-		-	μJ
E_{off}	Turn-off switching energy		-		-	
$t_{d(on)}$	Turn-on delay time		-		-	ns
t_r	Rise time		-		-	
$t_{d(off)}$	Turn-off delay time		-		-	
t_f	Fall time		-		-	
E_{on}	Turn-on switching energy	-		-	μJ	
E_{off}	Turn-off switching energy	-		-		

^b This SiC MOSFET can switch with driver pulses 0V to 20V with optimized PCB layouts and gate drive circuits.

Reverse SiC Diode Characteristics ($T_A = 25\text{ }^\circ\text{C}$, unless specified otherwise)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage					V
I_S	Continuous diode forward current					A
$I_{S, pulse}$	Diode pulse current					A
t_{rr}	Reverse recovery time					ns
Q_{rr}	Reverse recovery charge					μC
I_{rrm}	Peak reverse recovery current					A
t_{rr}	Reverse recovery time					ns
Q_{rr}	Reverse recovery charge					μC
I_{rrm}	Peak reverse recovery current					A

Electrical Characteristic Diagrams

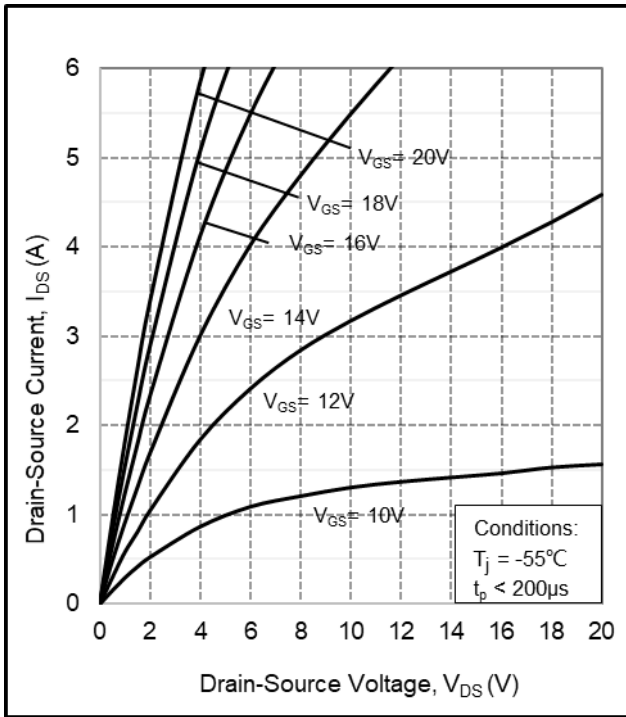


Figure 1. Output characteristics at $T_j = -55^\circ\text{C}$

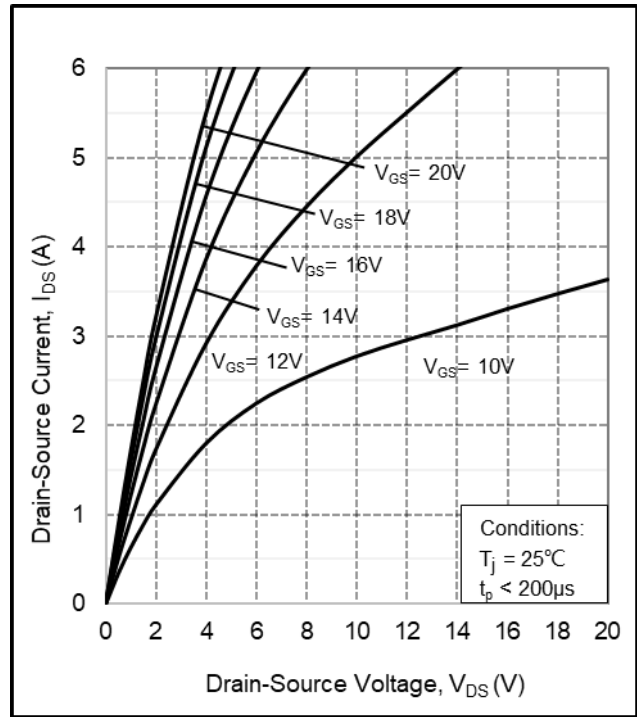


Figure 2. Output characteristics at $T_j = 25^\circ\text{C}$

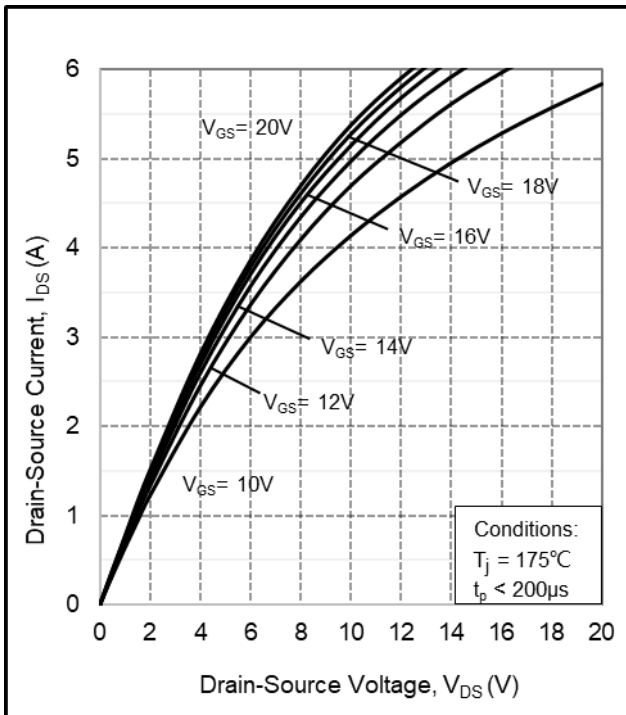


Figure 3. Output characteristics at $T_j = 175^\circ\text{C}$

Figure 4. Normalized on-resistance vs. temperature

Figure 5. On-resistance vs. drain current for various temperatures

Figure 6. On-resistance vs. temperature for various gate voltages

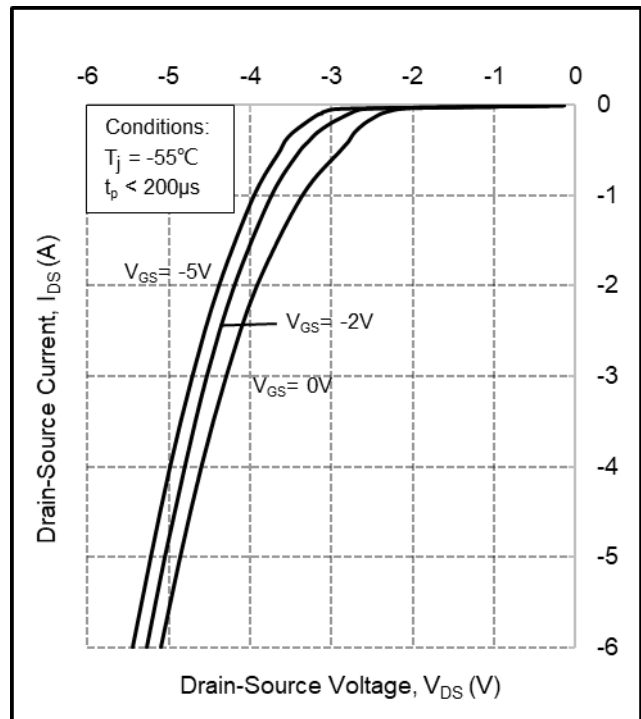


Figure 7. Transfer characteristic for various junction temperatures

Figure 8. Body diode characteristic at $T_j = -55^\circ\text{C}$

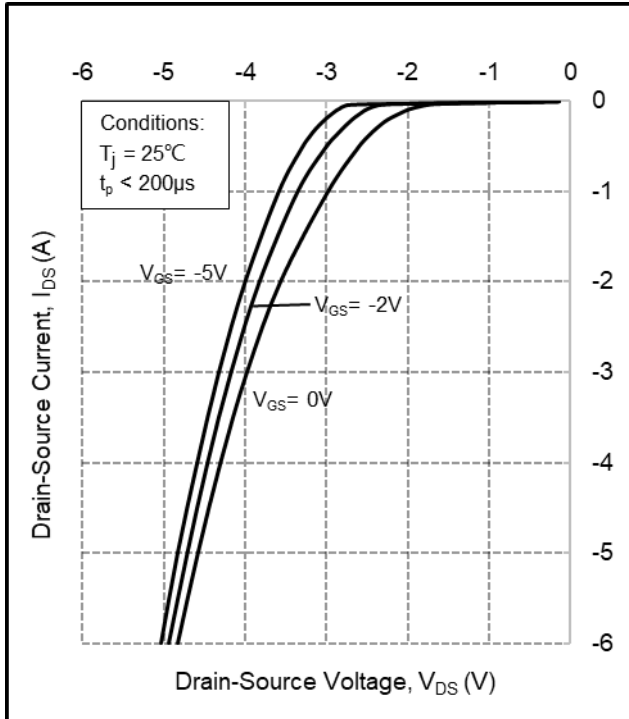


Figure 9. Body diode characteristic at $T_j = 25^\circ\text{C}$

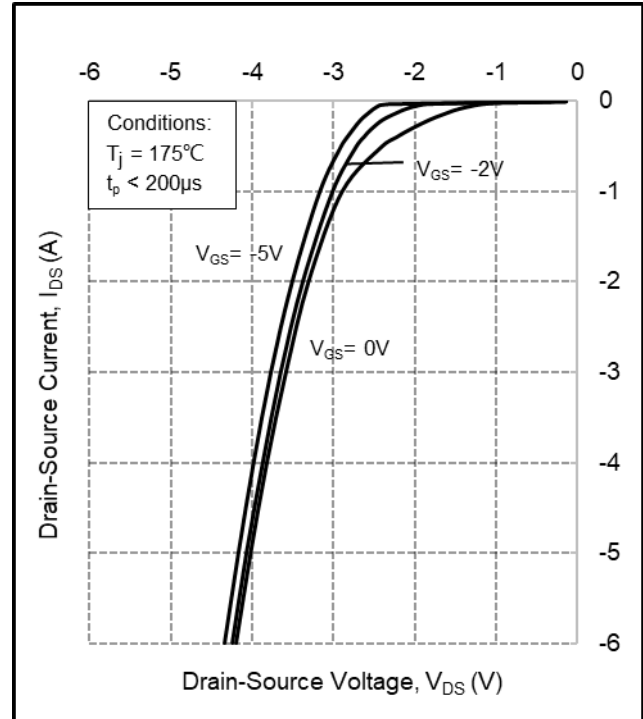


Figure 10. Body diode characteristic at $T_j = 175^\circ\text{C}$

Figure 11. Threshold voltage vs. temperature

Figure 12. Gate charge characteristics

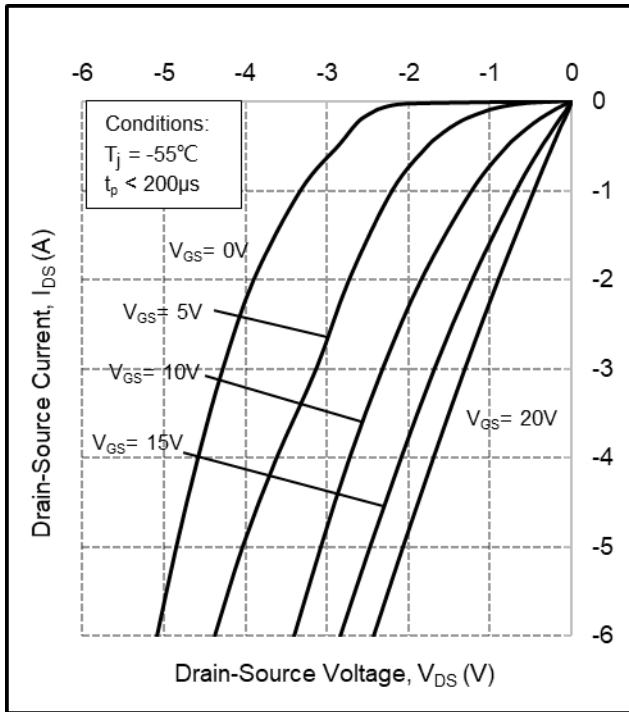


Figure 13. 3rd quadrant characteristic at $T_j = -55^\circ\text{C}$

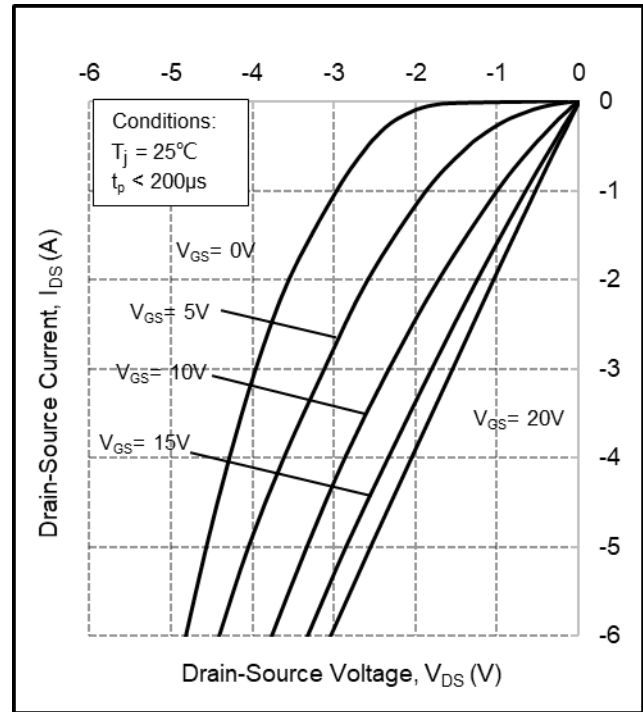


Figure 14. 3rd quadrant characteristic at $T_j = 25^\circ\text{C}$

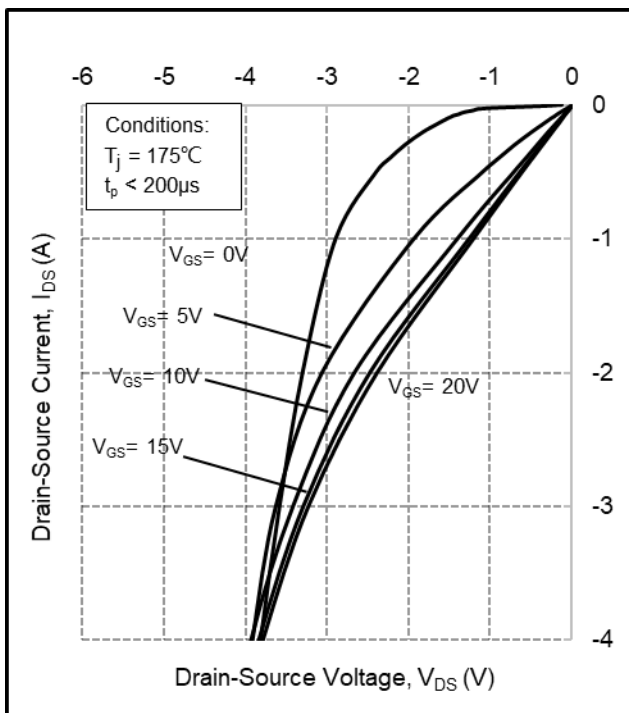


Figure 15. 3rd quadrant characteristic at $T_j = 175^\circ\text{C}$

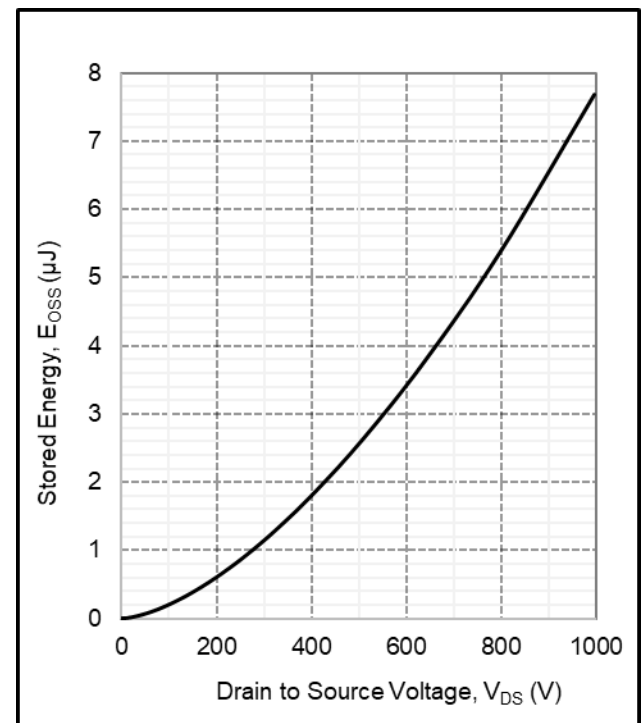


Figure 16. Output capacitor stored energy

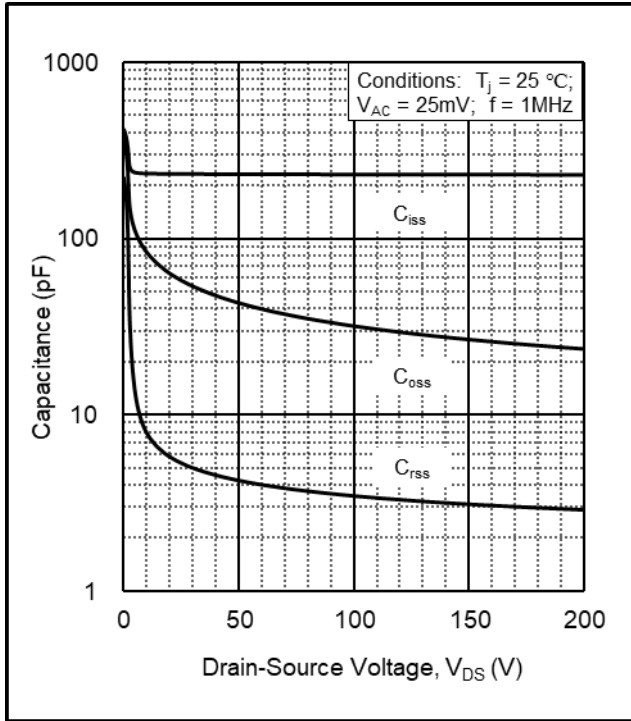


Figure 17. Capacitance vs. drain-source voltage (0 - 200V)

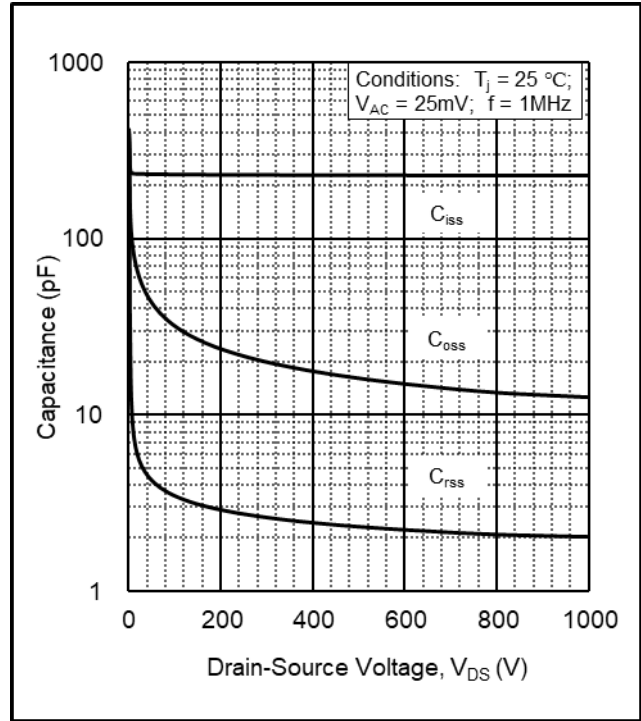


Figure 18. Capacitance vs. drain-source voltage (0 - 1000V)

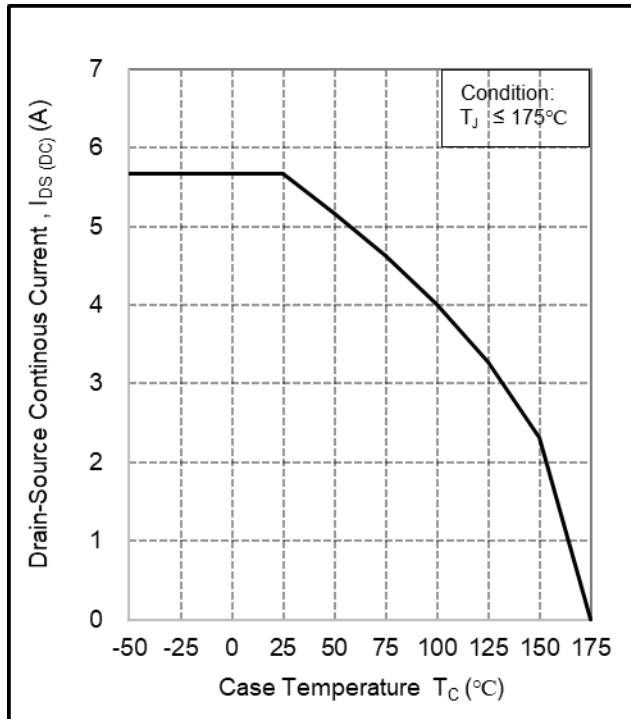


Figure 19. Continuous drain current derating vs. temperature

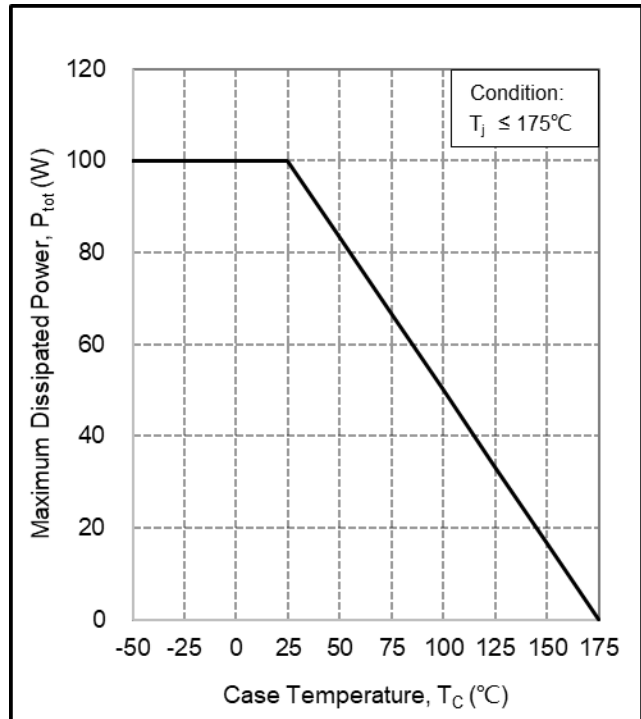


Figure 20. Maximum power dissipation derating vs. temperature

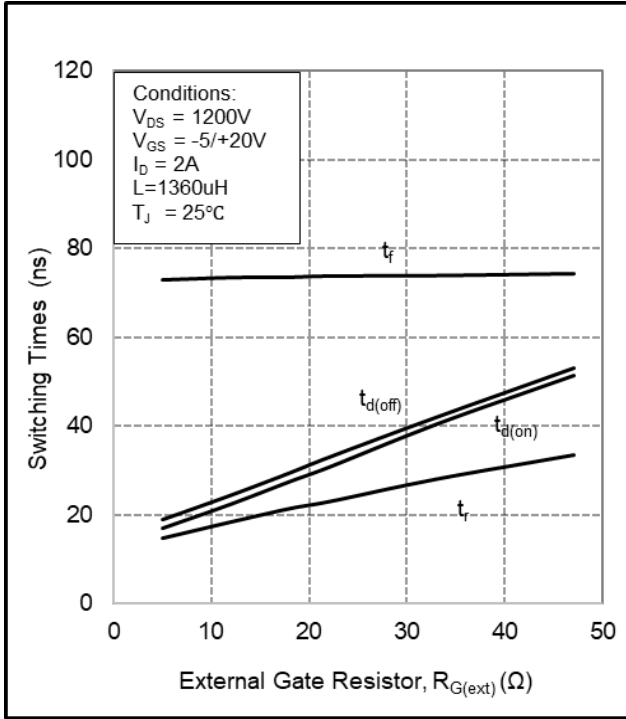


Figure 21. Switching Times vs. $R_{G(ext)}$

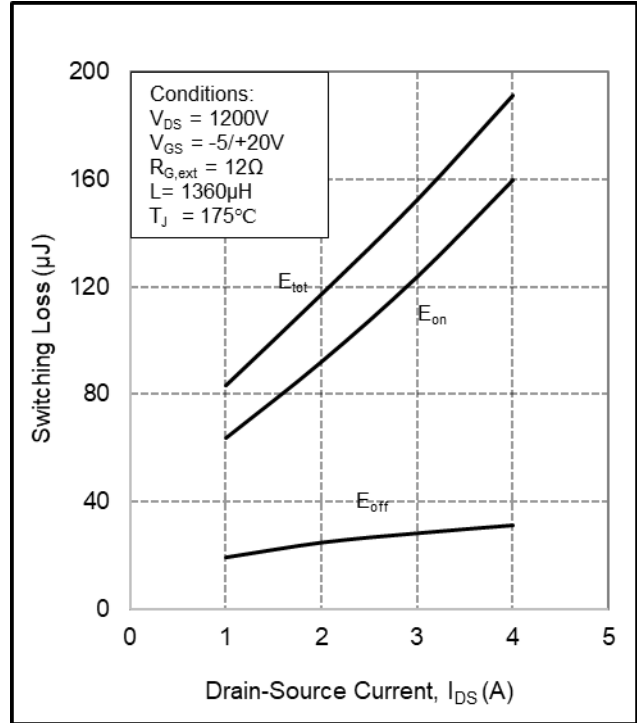


Figure 22. Clamped inductive Switching energy vs. drain current

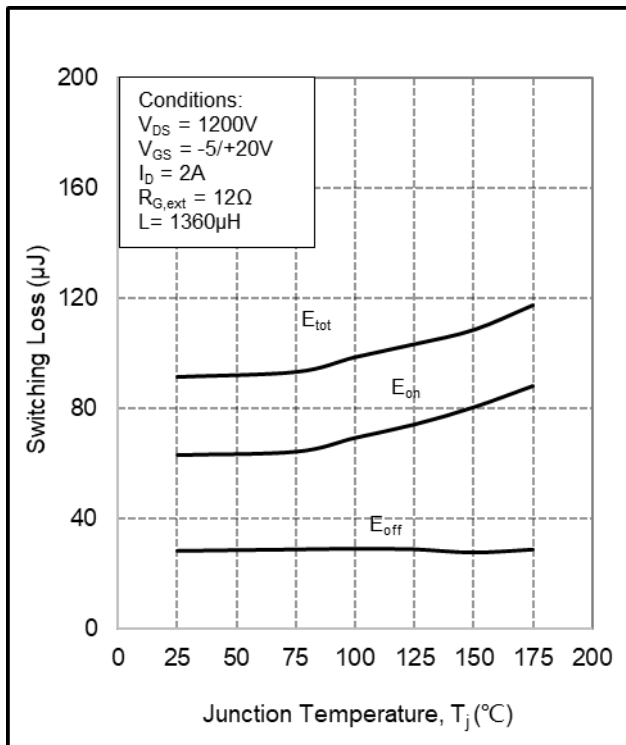


Figure 23. Clamped inductive Switching energy vs. temperature

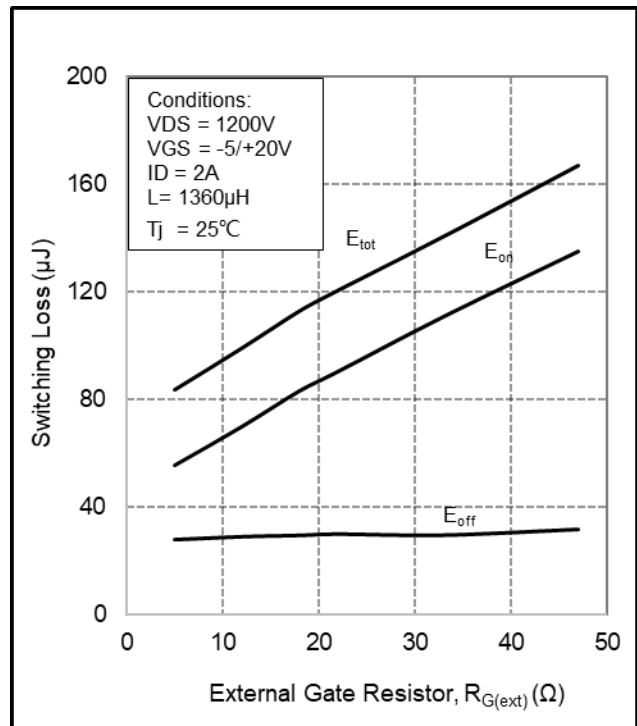


Figure 24. Clamped inductive Switching energy vs. $R_{G(ext)}$

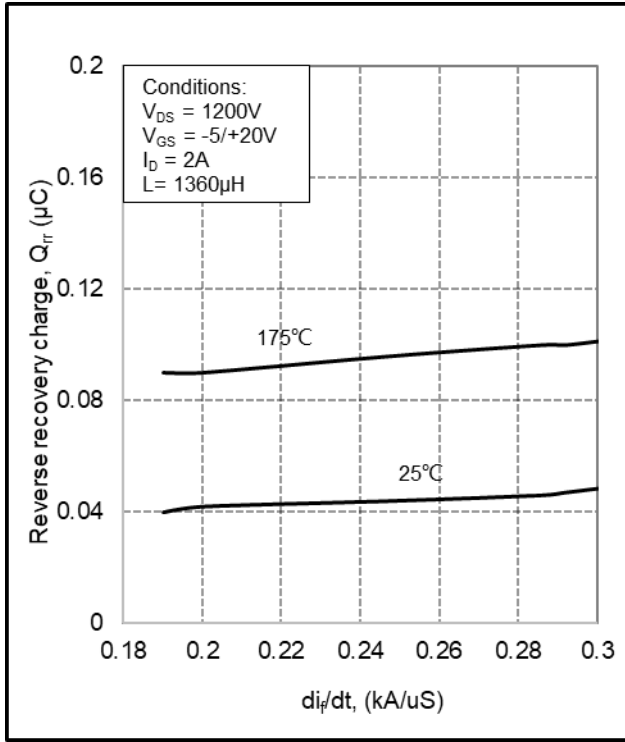


Figure 25. Reverse recovery charge vs. di_t/dt

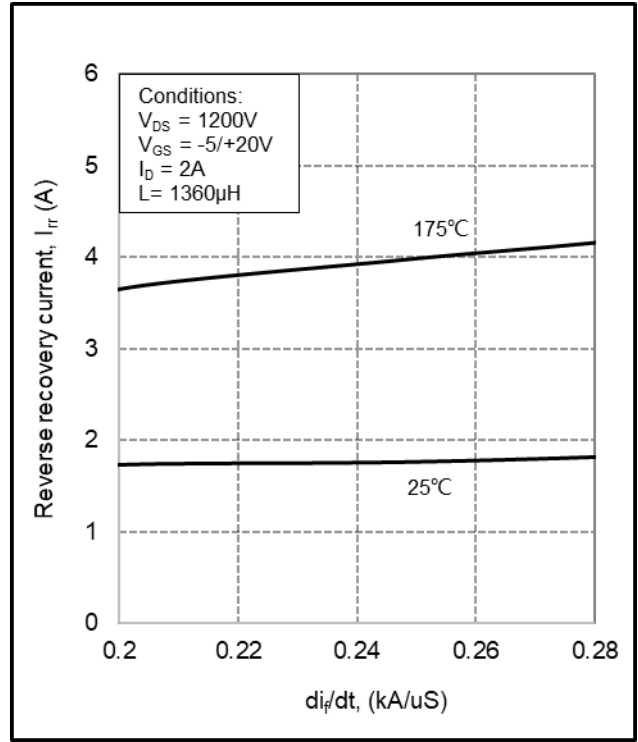


Figure 26. Reverse recovery current vs. di_t/dt

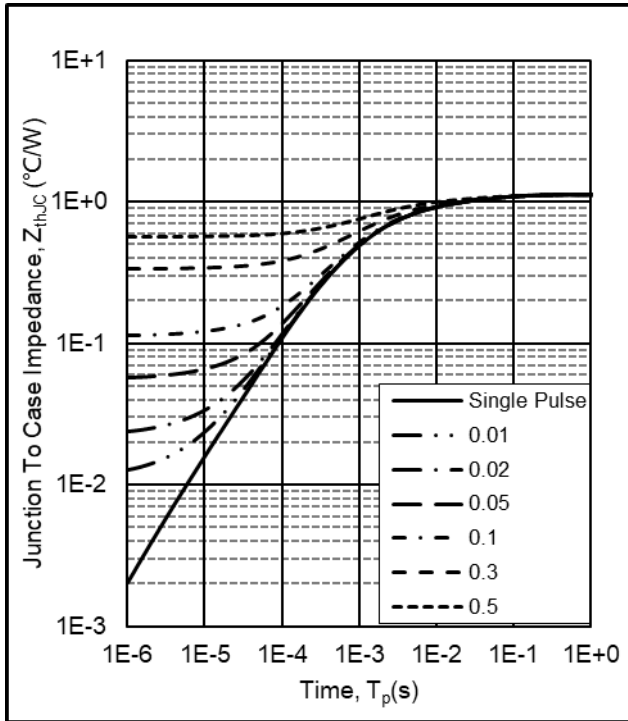


Figure 27. Transient Thermal Impedance (Junction - Case)

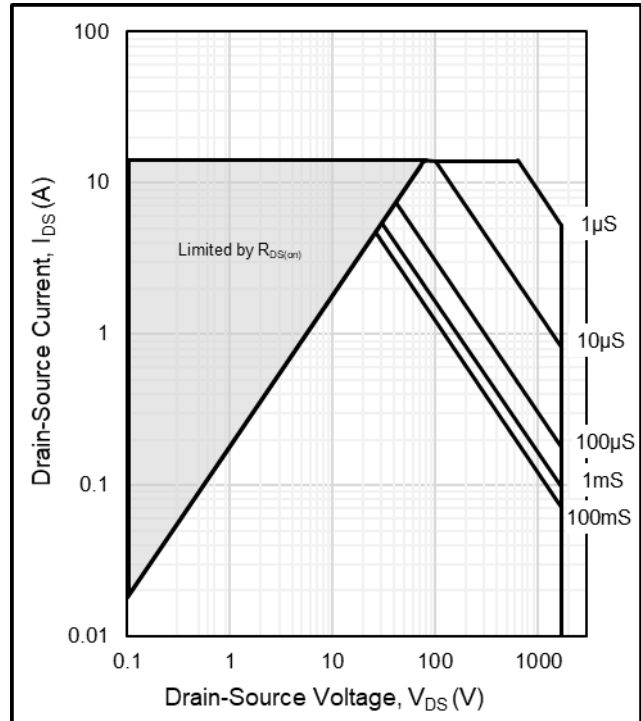


Figure 28. Safe Operating Area

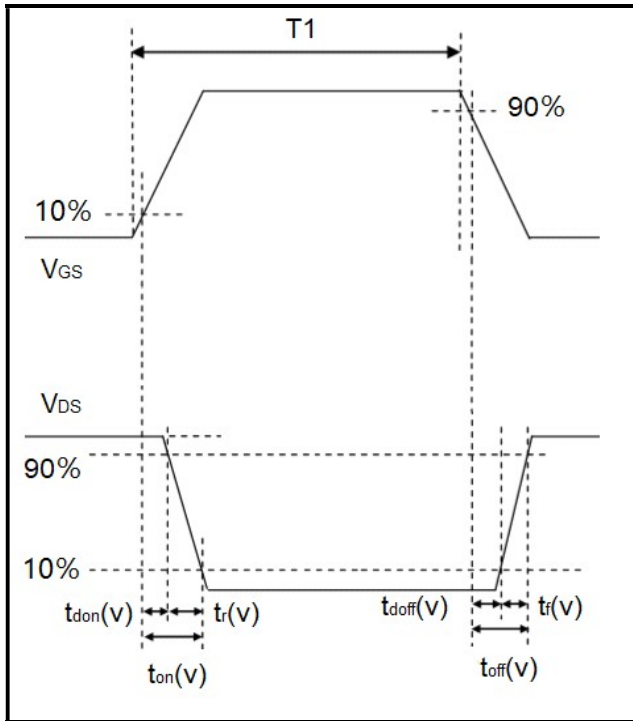


Figure 29. Switching times definition

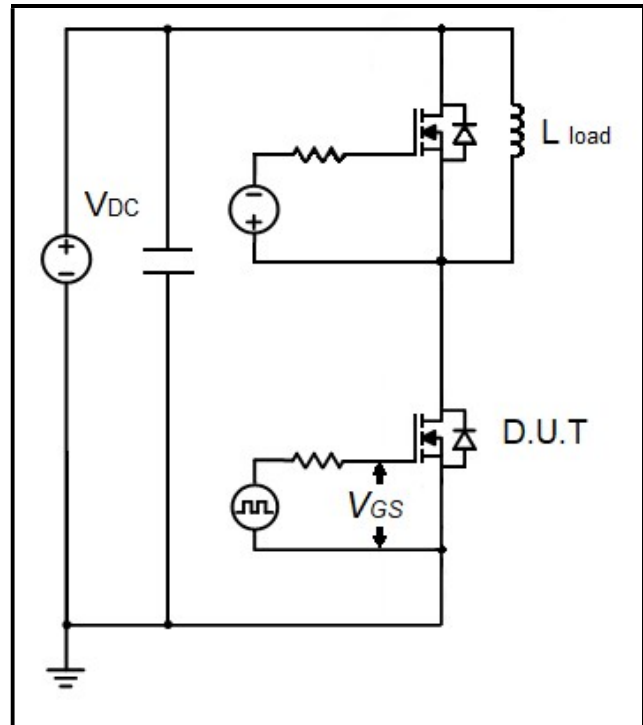


Figure 30. Clamped inductive switching waveform test circuit

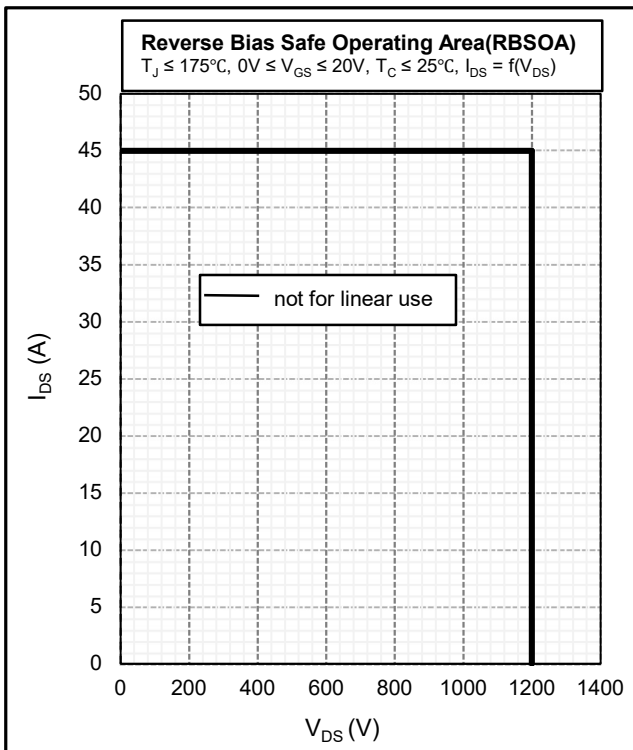
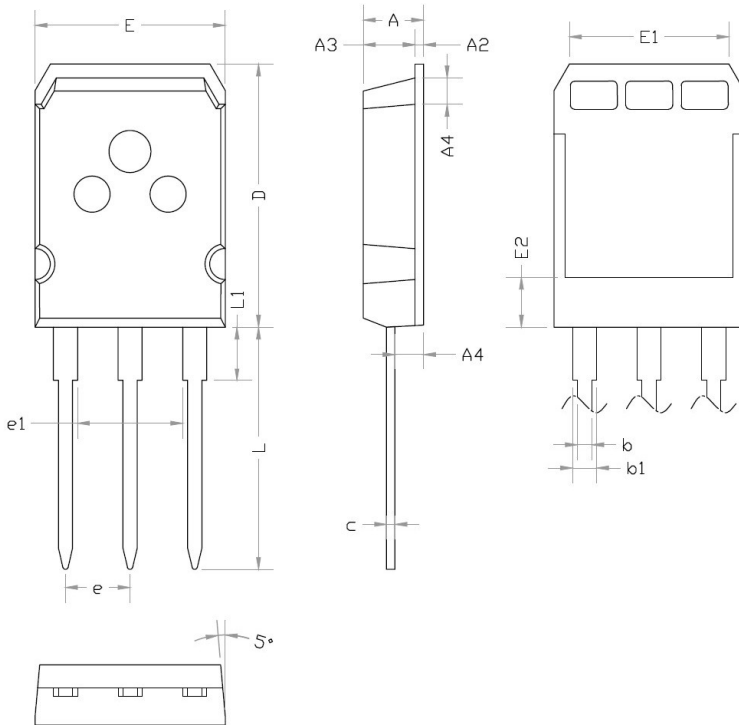


Figure 31. Reverse Bias Safe Operating Area

Package Information:



SYMBOL	mm
A	5.03 mm
A1	2.39 mm
A2	0.7 mm
A3	4.33 mm
A4	2.2 mm
b	1.19 mm
b1	2.01 mm
c	0.7 mm
D	21.94 mm
E	15.9 mm
E1	13.35 mm
E2	4.17 mm
e	5.4 mm
e1	8.79 mm
L	20.27 mm
L1	4.51 mm

Ordering Information

Part number	AMR1k0V170E1i
Package	TO-247i-3L
Unit quantity	300 EA
Packing type	Tube

For more information, visit <https://www.apowerc2.com>

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